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## On a One-Dimensional Steady-State Hydrodynamic Model for Semiconductors

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**Abstract.** We present a hydrodynamic model for semiconductors, where the energy equation is replaced by a pressure-density relationship. We prove existence of smooth solutions and a uniqueness result in the subsonic case, which is characterized by a smallness assumption on the current flowing through the device.

### 1. THE MODEL

The hydrodynamic model for semiconductors [1,2] has recently attracted a lot of attention because of its capability of modelling hot electron effects which are not accounted for in the classical drift-diffusion model [3,4]. A mathematical analysis of the hydrodynamic model has not been presented yet; only preliminary results exist by now [5]. In this paper, we investigate a simplified hydrodynamic model in which the energy equation is replaced by the assumption that the pressure is a given function of the density only. This assumption is commonly used in gas dynamics for isentropic or isothermal flows and gives Bernoulli's law [6].

After appropriate scaling the one-dimensional time-dependent system in the case of one carrier type (e.g. electrons) reads:

$$\rho_t + (\rho u)_x = 0 \quad (1.1)$$

$$(\rho u)_t + (\rho u^2 + p(\rho))_x - \rho \Phi_x = -\frac{\rho u}{\tau} \quad (1.2)$$

$$\Phi_{xx} = \rho - C(x), \quad (1.3)$$

where  $\rho(x, t)$ ,  $u(x, t)$ ,  $\Phi(x, t)$  denote the electron density, velocity, and the electrostatic potential respectively.  $p = p(\rho)$  is the pressure-density relation which satisfies:

$$\rho^2 p'(\rho) \text{ is strictly monotonically increasing from } [0, \infty[ \text{ onto } [0, \infty[. \quad (1.4)$$

A commonly used hypothesis is  $p(\rho) = \kappa \rho^\gamma$  where  $\gamma \geq 1$  and  $\kappa > 0$ .  $\tau = \tau(\rho, \rho u)$  is the momentum relaxation time of which we assume:

$$\tau(\rho, \rho u) \geq \tau_0 > 0 \quad \forall (\rho, \rho u) \in [0, \infty[ \times \mathbb{R}. \quad (1.5)$$

The device domain is the  $x$ -interval  $(0, 1)$ ;  $C = C(x) \in L^\infty(0, 1)$  is the doping profile (given background density), which satisfies  $C(x) > 0$ .

The system (1.1) to (1.3) is supplemented by the following boundary conditions:

$$\rho(0, t) = \rho_0, \quad \rho(1, t) = \rho_1 \quad (1.6)$$

$$\Phi(0, t) = 0, \quad \Phi(1, t) = \Phi_1 \quad (1.7)$$

The conditions (1.6) represent Ohmic contacts, and  $\Phi_1$  stands for the applied bias.

In this paper, we investigate the steady state case  $\rho_t = (\rho u)_t = 0$ . Then, introducing the current density  $j = \rho u$ , the system (1.1) to (1.3) reduces to

$$j(x) = \text{const.} \quad (1.8)$$

$$\left( \frac{j^2}{\rho} + p(\rho) \right)_x - \rho \Phi_x = -\frac{j}{\tau} \quad (1.9)$$

$$\Phi_{xx} = \rho - C(x). \quad (1.10)$$

Up to now, the system (1.8) to (1.10) is valid for the cases of discontinuous as well as regular solutions. For the case of regular solutions we recast (1.9) by differentiating, dividing by  $\rho$  and using (1.8). We obtain

$$\left( \frac{j^2}{2\rho^2} + h(\rho) - \Phi \right)_x + \frac{j}{\tau\rho} = 0, \quad h'(\rho) = \frac{1}{\rho} p'(\rho). \quad (1.11)$$

Integrating this equation over  $(0, 1)$  and using (1.6), (1.7) leads to the following current-voltage characteristic:

$$\Phi_1 = F(\rho_1, j) - F(\rho_0, j) + j \int_0^1 \frac{dx}{\tau(\rho(x), j)\rho(x)} \quad (1.12)$$

where we denoted

$$F(\rho, j) = \frac{j^2}{2\rho^2} + h(\rho). \quad (1.13)$$

The relation (1.12) shows that we can prescribe  $j$  instead of  $\Phi_1$ . Then by differentiating (1.11) and using the Poisson equation (1.10), we obtain the following second order boundary value problem, parametrized by  $j \in \mathfrak{R}$ :

$$F(\rho, j)_{xx} + j \left( \frac{1}{\tau\rho} \right)_x - \rho = -C(x), \quad 0 < x < 1, \quad (1.14)$$

$$\rho(0) = \rho_0, \quad \rho(1) = \rho_1. \quad (1.15)$$

Once  $\rho$  is known from (1.14), (1.15),  $\Phi$  can be computed by solving the Poisson equation (1.10) using the boundary condition (1.12) and  $\Phi(0) = 0$ . Thus, finding regular steady-state solutions of the hydrodynamic model (1.1) to (1.7) amounts to solving (1.14)-(1.15).

**Remark 1.** The equation (1.9) can be regarded as a modified steady-state drift-diffusion model with a nonlinear current dependent diffusion term.

## 2. EXISTENCE IN THE SUBSONIC CASE

Since we have

$$\frac{\partial F}{\partial \rho}(\rho, j) = -\frac{j^2}{\rho^3} + \frac{1}{\rho} p'(\rho) > 0 \Leftrightarrow \rho^2 p'(\rho) > j^2 \quad (2.1)$$

We conclude from (1.4) that there exists a unique  $\rho_m = \rho_m(j) \geq 0$  such that  $\frac{\partial F}{\partial \rho}(\rho, j) > 0$  for  $\rho > \rho_m$ . A typical plot of  $\rho \rightarrow F(\rho, j)$  for fixed  $|j| > 0$  is shown in Figure 1. Note that, by (2.1), the minimal point  $\rho_m$  of  $\rho \rightarrow F(\rho, j)$  is a strictly increasing function of  $j$ , and  $\rho_m(j=0) = 0$ .

The preceding considerations show that the equation (1.14) is uniformly elliptic for  $\rho \geq \rho^* > \rho_m$ . By (2.1), this condition implies  $|u| < c$  where  $c = (p'(\rho))^{\frac{1}{2}}$  denotes the speed of sound. Thus, the following theory applies to a fully subsonic flow. We prove an existence result in this case:

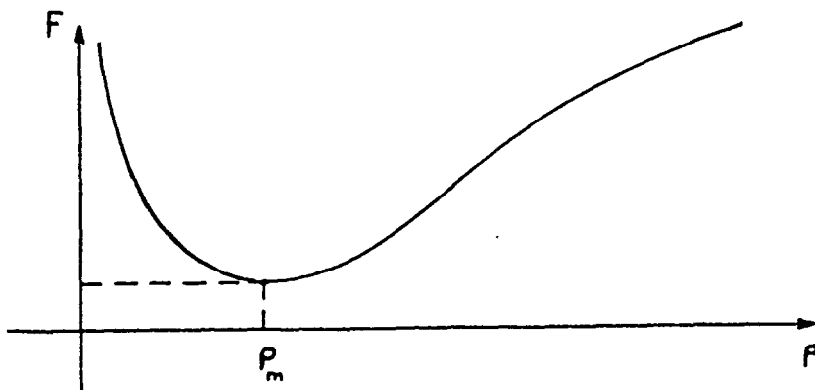


Figure 1: Plot of  $\rho \rightarrow F(\rho, j)$ .

**THEOREM 1.**

Let the assumptions (1.4), (1.5),  $C \in L^\infty(0, 1)$  hold and additionally assume that  $p'$ ,  $\tau$  and  $\partial\tau/\partial\rho$  are continuous with respect to  $\rho$ . Let  $j$  be such that

$$\rho_0, \rho_1, \inf_{x \in (0,1)} C(x) > \rho_m(j). \tag{2.2}$$

Then, the problem (1.14), (1.15) has a solution which satisfies

$$\text{Min}(\rho_0, \rho_1, \underline{C}) \leq \rho(x) \leq \text{Max}(\rho_0, \rho_1, \overline{C}), \quad x \in [0, 1] \tag{2.3}$$

where

$$\underline{C} := \inf_{x \in [0,1]} C(x), \quad \overline{C} := \sup_{x \in [0,1]} C(x).$$

**Remark 2.** By the above discussion of  $\rho_m$ , there exists a unique current  $j_M$  such that (2.2) is equivalent to  $|j| < j_M$ .  $j_M$  is given by

$$\rho_m(j_M) = \text{Min}(\rho_0, \rho_1, \underline{C}).$$

Thus, (2.2) represents a smallness assumption on the current flowing through the device, and gives a condition for fully subsonic flow.

*Proof:* We consider the operator  $T : \Psi \rightarrow \rho$  defined by solving

$$\left( \frac{\partial F}{\partial \rho}(\Psi, j) \rho_x \right)_x - jG(\Psi, j) \rho_x - \rho = -C, \quad 0 < x < 1, \tag{2.4}$$

$$\rho(0) = \rho_0, \quad \rho(1) = \rho_1, \tag{2.5}$$

where we denoted

$$G(\rho, j) = \frac{\frac{\partial \tau}{\partial \rho}(\rho, j) \rho + \tau(\rho, j)}{\tau(\rho, j)^2 \rho^2}. \tag{2.6}$$

Now, suppose that  $\Psi$  satisfies

$$\rho_s := \text{Min}(\rho_0, \rho_1, \underline{C}) \leq \Psi \leq \rho_u := \text{Max}(\rho_0, \rho_1, \overline{C}). \tag{2.7}$$

By the assumption (2.2), the linear equation (2.4) is uniformly elliptic. Thus, the smoothness assumptions on  $p$  and  $\tau$  guarantee the existence of a unique  $H^1(0, 1)$ -solution  $\rho$ . The maximum principle [7] implies that  $\rho = T(\Psi)$  also satisfies (2.7). Then, by multiplying (2.4) by  $(\rho - \rho_B)$  where  $\rho_B$  is any function assuming the boundary conditions an  $H^1(0, 1)$  bound on  $\rho$  independent of  $\Psi$  is easily obtained. By the compact imbedding of  $H^1(0, 1)$  into  $C^0([0, 1])$ , and by a standard continuity argument we conclude the existence of a fixed point of  $T$  from Schauder's theorem. ■

**Remark 3.** If  $|j|$  is so large that the condition (2.2) is violated, then the flow may at least be partly supersonic and the occurrence of shocks cannot be excluded.

3. UNIQUENESS FOR SMALL  $|j|$ 

We prove the following uniqueness result for small currents.

## THEOREM 2.

Let the assumptions of Theorem 1 hold, and additionally assume that  $\tau$  and  $\partial\tau/\partial\rho$  are jointly continuous with respect to  $(\rho, j)$ . Then, there exists a constant  $j_0 > 0$  such that for any current which satisfies  $|j| < j_0$ , there exists at most one regular solution  $\rho$  of the problem (1.14), (1.15) in the set of functions which satisfy  $\rho(x) \geq \rho^* > \rho_m(j)$  for all  $x$  in  $[0, 1]$ .

*Proof:* Let  $\rho_1$  and  $\rho_2$  be two solutions of the problem (1.14), (1.15) which satisfy  $\rho_i(x) \geq \rho^* > \rho_m(j)$  for  $i = 1, 2$ . Then by subtracting the equations we obtain:

$$(a(x)e)_{xx} + j(b(x)e)_x - e = 0 \quad (3.1)$$

where  $e(x) = (\rho_2 - \rho_1)(x)$  and

$$a(x) = \int_0^1 \frac{\partial F}{\partial \rho}(\rho_1(x) + v(\rho_2(x) - \rho_1(x)), j) dv \quad (3.2)$$

$$b(x) = \frac{1}{\tau(\rho_1, j)\rho_1\tau(\rho_2, j)\rho_2} \int_0^1 \frac{\partial(\rho\tau(\rho, j))}{\partial \rho}(\rho_1(x) + v(\rho_2(x) - \rho_1(x))) dv. \quad (3.3)$$

Multiplying (3.1) by  $ae$  and integration by parts give:

$$\int_0^1 |(ae)_x|^2 dx + j \int_0^1 b(x)e(ae)_x dx + \int_0^1 a|e|^2 dx = 0. \quad (3.4)$$

We estimate, using the positivity of  $a$ :

$$\begin{aligned} \left| \int_0^1 b(x)e(ae)_x dx \right| &\leq \frac{1}{2} \int_0^1 |b(x)|\sqrt{a(x)}|e(x)|^2 dx \\ &\quad + \frac{1}{2} \int_0^1 \frac{|b(x)|}{\sqrt{a(x)}} |(ae)_x|^2 dx. \end{aligned} \quad (3.5)$$

Thus we obtain:

$$\begin{aligned} &\int_0^1 \left( 1 - \frac{|j|}{2} \frac{|b(x)|}{\sqrt{a(x)}} \right) |(ae)_x|^2 dx \\ &+ \int_0^1 \left( a(x) - \frac{|j|}{2} |b(x)|\sqrt{a(x)} \right) |e|^2 dx \leq 0. \end{aligned} \quad (3.6)$$

Both terms on the left hand side are positive if

$$|j||b(x)| \leq \sqrt{a(x)}. \quad (3.7)$$

By the assumptions of Theorem 2, there exists a constant  $j_0 > 0$  such that (3.7) holds for any  $|j| \leq j_0$ .

**Remark 4.** The condition (3.7) can also be regarded as a condition on  $\tau$ : for a given  $j$ , uniqueness holds if  $\tau$  is sufficiently large and constant. In particular, for  $\tau = \infty$  (infinitely fast momentum relaxation), we have uniqueness for all  $j$  in the subsonic regime.

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